Gunter Semiconductor GmbH	**SB 1XX - 1.3** **Chips for Schottky Diodes**

Chip Specification

General Description:

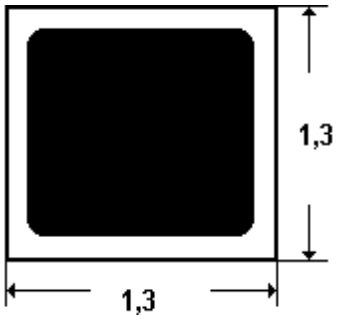
Schottky Diode chips with Mo-barrier for switch mode power rectifiers with the following features:

*** Guard-ring for stress protection**
*** Extremely low forward voltage**
*** 125 ℃ operation junction temperature**
*** reverse avalanche behavior**

Mechanical Data:

SB 1XX passivated Silicon Chip

Demension(mm)	1,3x1,3
Thickness:	350 +- 20 µm
Metallization:	
Top (Anode) :	Al Ag
Bottom (Cathode) :	TiNiAg



Forward Current(A)	1 A
Reverse Voltage (V):	23, 43, 100 V

Type	Chip size(mm)	V_R(V)	VF(V)@25 C at If=1A	$I_{RM}@V_{RMM}$ at 25 C
SB120	1,3x1,3	23 V	380mV	0,5mA
SB140	1,3x1,3	43 V	400mV	0,5mA
SB1100	1,3x1,3	100 V	650mV	0,5mA

Note: Other voltages, Vf & Top Metal AL are available